

Device Modeling Report

COMPONENTS: THYRISTOR
PART NUMBER: 2N6509
MANUFACTURER: ON SEMICONDUCTOR



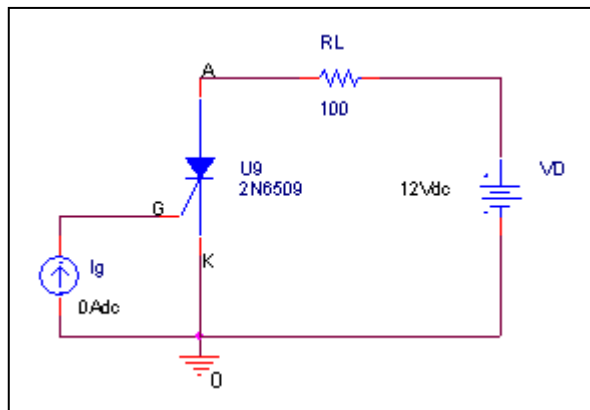
Bee Technologies Inc.

DIODE MODEL

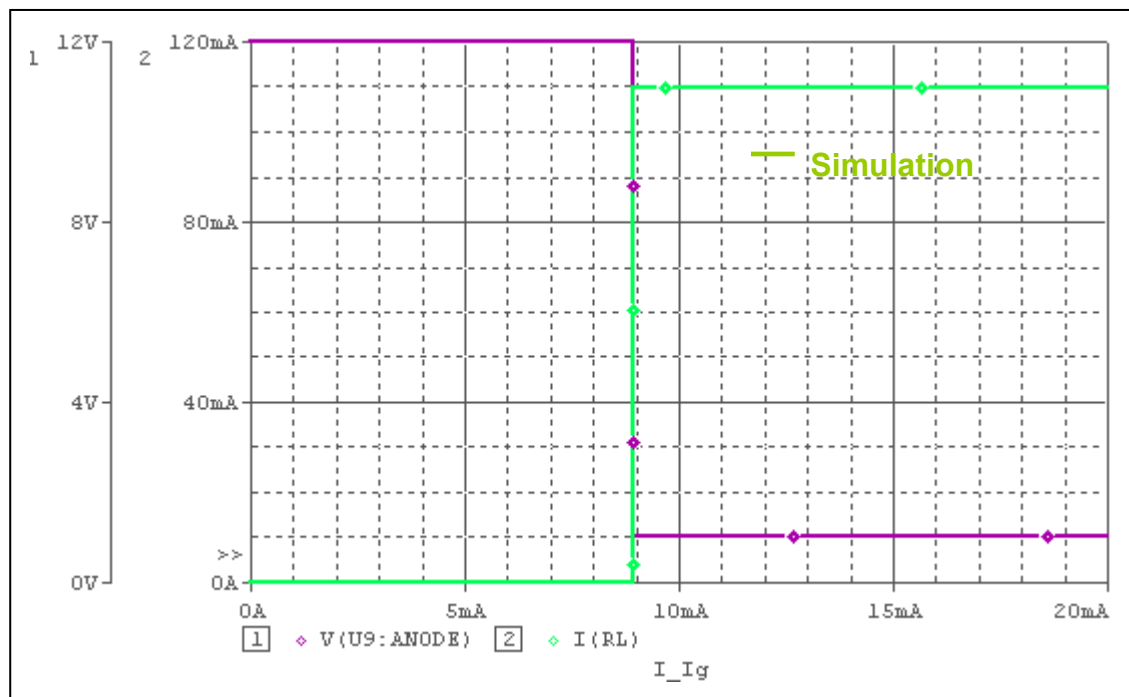
Pspice model Parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

IG-VT Characteristic

Evaluation Circuit



Simulation result

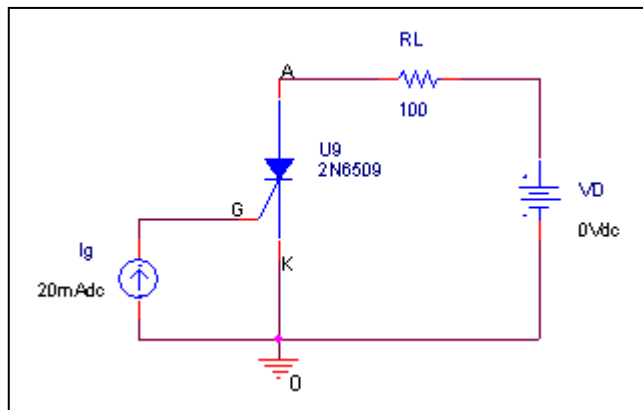


Comparison Table

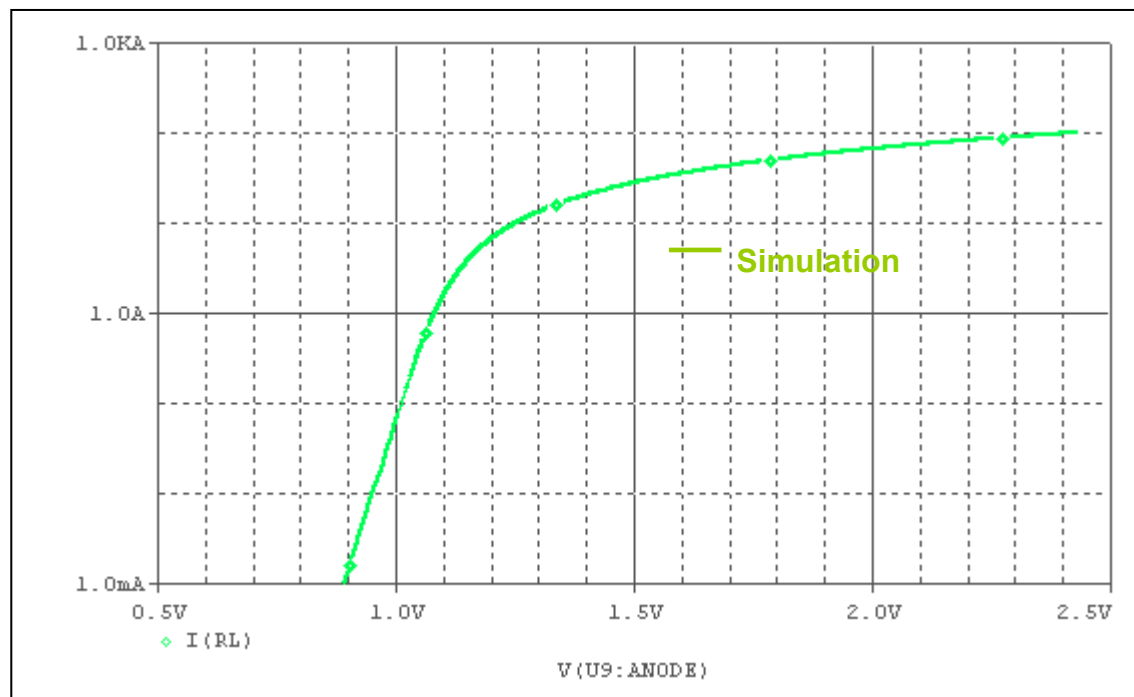
	Measurement	Simulation	% Error
I_{GT} (mA)	9	8.9300	-0.77778
V_{GT} (V)	1.0	1.0135	1.35000

ITM-VTM Characteristic

Evaluation Circuit



Simulation result

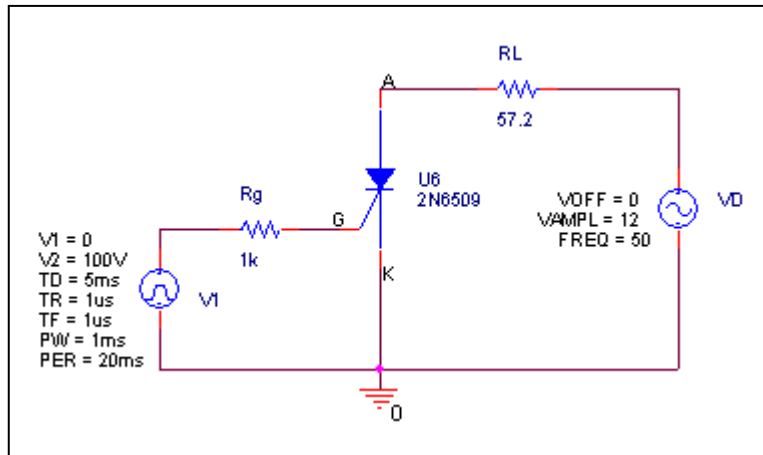


Comparison Table

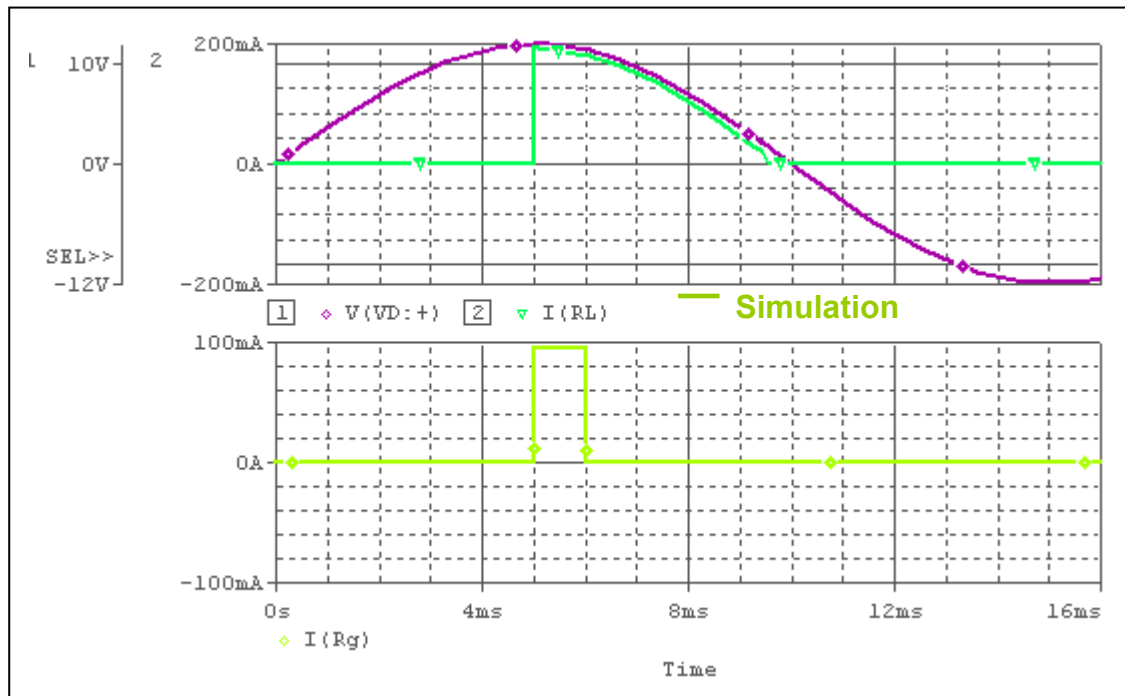
At ITM=50	Measurement	Simulation	% Error
VTM(V)	1.8(max)	1.7919	-0.45000

Holding Characteristic (IH)

Evaluation Circuit



Simulation result

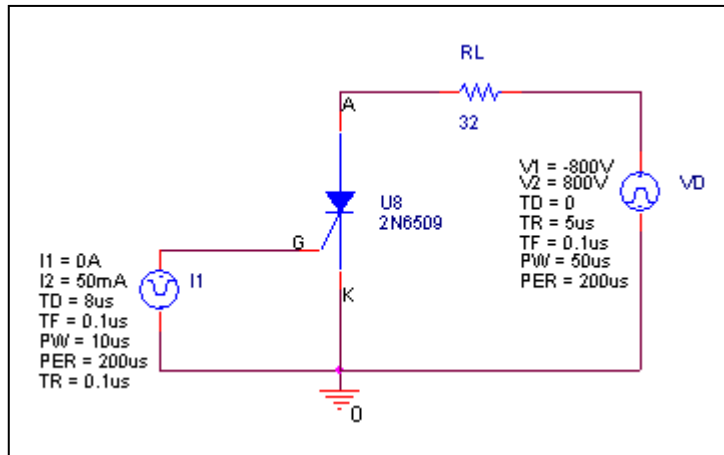


Comparison Table

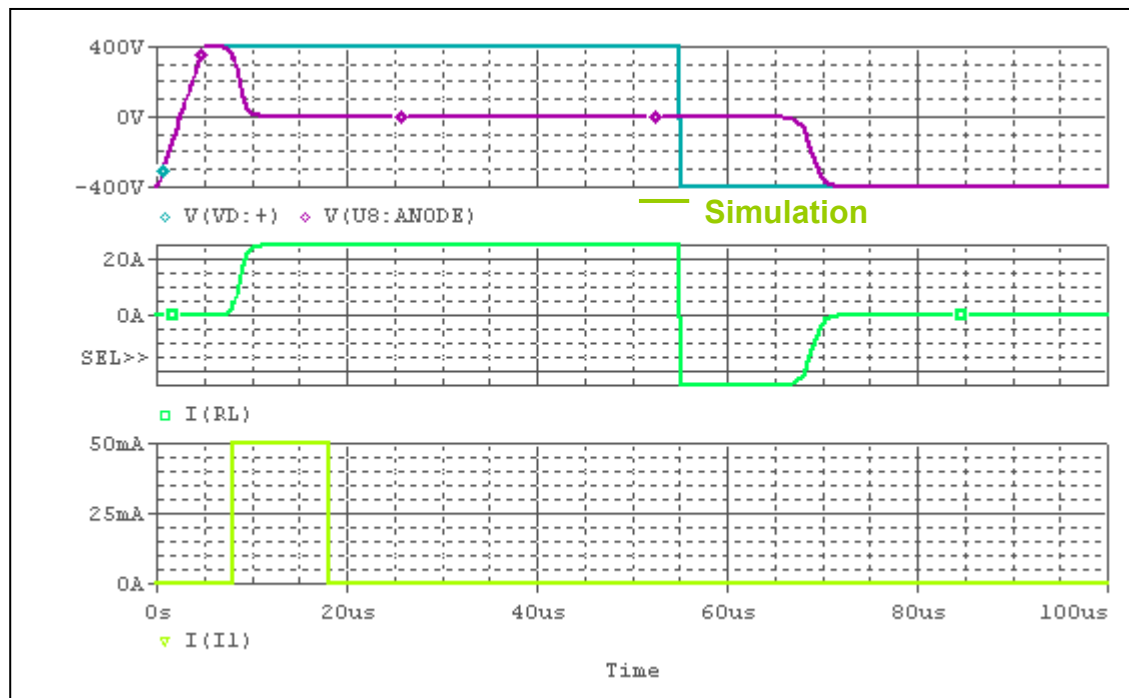
VD=12V	Measurement	Simulation	% Error
IH(mA)	18	17.526	-2.63333

Switching Time Characteristic

Evaluation Circuit



Simulation result



Comparison Table

	Measurement	Simulation	%Error
Ton(us)	1.5	1.5455	3.03333
Toff(us)	15	15.014	0.09333